PROCEEDINGS OF SPIE

Advances in Patterning Materials and Processes XLI

Douglas Guerrero
Gilles R. Amblard
Editors

26–29 February 2024
San Jose, California, United States

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IBM Corporation (United States)
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Published by
SPIE

Volume 12957

Proceedings of SPIE 0277-786X, V. 12957

SPIE is an international society advancing an interdisciplinary approach to the science and application of light.

Advances in Patterning Materials and Processes XLI, edited by Douglas Guerrero, Gilles R. Amblard, Proc. of SPIE Vol. 12957, 1295701 · © 2024 SPIE
0277-786X · doi: 10.1117/12.3031878

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Please use the following format to cite material from these proceedings:
Author(s), "Title of Paper," in *Advances in Patterning Materials and Processes XLI*, edited by Douglas Guerrero, Gilles R. Amblard, Proc. of SPIE 12957, Seven-digit Article CID Number (DD/MM/YYYY); (DOI URL).

ISSN: 0277-786X
ISSN: 1996-756X (electronic)

ISBN: 9781510672208
ISBN: 9781510672215 (electronic)

Published by
SPIE
P.O. Box 10, Bellingham, Washington 98227-0010 USA
Telephone +1 360 676 3290 (Pacific Time)
SPIE.org
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